NPN Silicon Power Darlington Transistors

The MJE5740, 41, 42 Darlington transistors are designed for high-voltage power switching in inductive circuits. They are particularly suited for operation in applications such as:

- · Small Engine Ignition
- Switching Regulators
- Inverters
- · Solenoid and Relay Drivers
- Motor Controls

MAXIMUM RATINGS

Rating	Symbol	MJE5740	MJE5741	MJE5742	Unit	
Collector–Emitter Voltage	VCEO(sus)	300	350	400	Vdc	
Collector–Emitter Voltage	VCEV	600	700	800	Vdc	
Emitter Base Voltage	V _{EB}	8		Vdc		
Collector Current — Continuous — Peak (1)	I _C	8 16				
Base Current — Continuous — Peak (1)	I _B I _{BM}	2.5 5		· ·		Adc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2 16		Watts mW/°C		
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	80 640		Watts mW/°C		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150		°C		

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle = 10%.

THERMAL CHARACTERISTICS

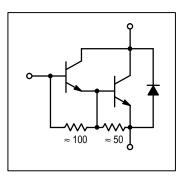
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.56	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	275	°C

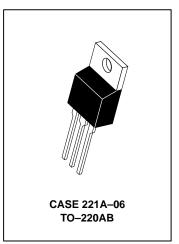
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

MJE5740
MJE5741*
MJE5742*

*Motorola Preferred Device

POWER DARLINGTON TRANSISTORS 8 AMPERES 300, 350, 400 VOLTS 80 WATTS





Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS (2)						
Collector–Emitter Sustaining Voltage (I _C = 50 mA, I _B = 0)	MJE5740 MJE5741 MJE5742	VCEO(sus)	300 350 400	_ _ _		Vdc
Collector Cutoff Current (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc) (V _{CEV} = Rated Value, V _{BE(off)} = 1.5 Vdc, T _C = 100°C)		ICEV	_ _	_	1 5	mAdc
Emitter Cutoff Current (V _{EB} = 8 Vdc, I _C = 0)		I _{EBO}	_	_	75	mAdc
SECOND BREAKDOWN						
Second Breakdown Collector Current with Base Forward Biased		I _{S/b}		See Fig	gure 6	

RBSOA

Clamped Inductive SOA with Base Reverse Biased (2) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

(continued)

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 1



See Figure 7

MJE5740 MJE5741 MJE5742

ELECTRICAL CHARACTERISTICS — **continued** ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS (1)					
DC Current Gain ($I_C = 0.5$ Adc, $V_{CE} = 5$ Vdc) ($I_C = 4$ Adc, $V_{CE} = 5$ Vdc)	hFE	50 200	100 400	_ _	_
Collector–Emitter Saturation Voltage (IC = 4 Adc, IB = 0.2 Adc) (IC = 8 Adc, IB = 0.4 Adc) (IC = 4 Adc, IB = 0.2 Adc, TC = 100° C)	VCE(sat)	_ _ _	_ _ _	2 3 2.2	Vdc
Base–Emitter Saturation Voltage (I_C = 4 Adc, I_B = 0.2 Adc) (I_C = 8 Adc, I_B = 0.4 Adc) (I_C = 4 Adc, I_B = 0.2 Adc, I_C = 100°C)	VBE(sat)	_ _ _	_ _ _	2.5 3.5 2.4	Vdc
Diode Forward Voltage (2) (I _F = 5 Adc)	V _f	_	_	2.5	Vdc

SWITCHING CHARACTERISTICS

Typical Resistive Load (Ta	ible 1)					
Delay Time		t _d	ı	0.04	_	μs
Rise Time	$(V_{CC} = 250 \text{ Vdc}, I_{C(pk)} = 6 \text{ A})$	t _r		0.5	_	μs
Storage Time	$(V_{CC} = 250 \text{ Vdc}, I_{C(pk)} = 6 \text{ A}$ $I_{B1} = I_{B2} = 0.25 \text{ A}, t_p = 25 \mu\text{s},$ Duty Cycle $\leq 1\%$	t _S		8	_	μs
Fall Time	,	t _f		2	_	μs
Inductive Load, Clamped (Table 1)						
Voltage Storage Time	$(I_{C(pk)} = 6 \text{ A}, V_{CE(pk)} = 250 \text{ Vdc}$	t _{SV}		4	_	μs
Crossover Time	$(I_{C(pk)} = 6 \text{ A}, V_{CE(pk)} = 250 \text{ Vdc}$ $I_{B1} = 0.06 \text{ A}, V_{BE(off)} = 5 \text{ Vdc})$	t _C	l	2	_	μs

- (1) Pulse Test: Pulse Width 300 μ s, Duty Cycle = 2%.
- (2) The internal Collector–to–Emitter diode can eliminate the need for an external diode to clamp inductive loads. Tests have shown that the Forward Recovery Voltage (V_f) of this diode is comparable to that of typical fast recovery rectifiers.

TYPICAL CHARACTERISTICS

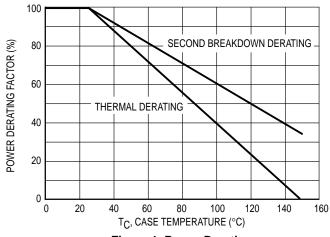


Figure 1. Power Derating

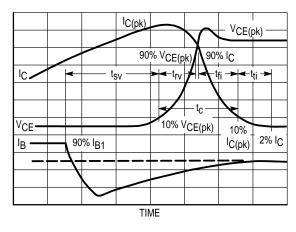


Figure 2. Inductive Switching Measurements

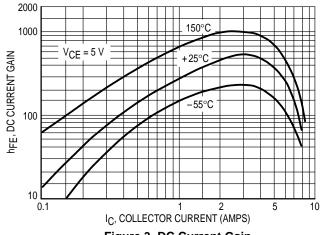


Figure 3. DC Current Gain

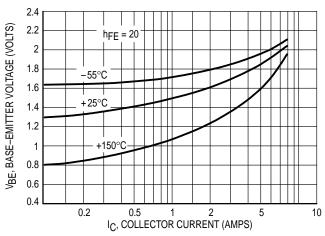


Figure 4. Base-Emitter Voltage

Table 1. Test Conditions for Dynamic Performance

	REVERSE BIAS SAFE OPERATING AREA AND INDUCTIVE SWITCHING	RESISTIVE SWITCHING
TEST CIRCUITS	DUTY CYCLE \leq 10% $_{1}$ $_{1}$ $_{2}$ $_{1}$ $_{2}$ $_{1}$ $_{2}$ $_{1}$ $_{2}$ $_{2}$ $_{1}$ $_{2}$ $_{3}$ $_{3}$ $_{3}$ $_{1}$ $_{1}$ $_{4}$ $_{2}$ $_{$	+VCC RC SCOPE -4 V
CIRCUIT	COIL DATA: GAP FOR 200 μ H/20 A FERROXCUBE CORE #6656 FULL BOBBIN (~16 TURNS) #16 CQAP FOR 200 μ H/20 A $V_{CE(pk)} = 250 \text{ Vdc}$ $V_{C(pk)} = 6 \text{ A}$	V _{CC} = 250 V D1 = 1N5820 OR EQUIV.
TEST WAVEFORMS	OUTPUT WAVEFORMS $t_{1} \text{ ADJUSTED TO} \\ \text{OBTAIN } I_{C} \\ \text{VCE} \\ \text{VCE} \\ \text{VCIAMP} \\ \text{TIME} \\ \text{VCIAMP} \\ t_{2} \approx \frac{L_{coil} (C_{pk})}{V_{clamp}}$ $t_{1} \text{ ADJUSTED TO} \\ \text{OBTAIN } I_{C} \\ \text{TEST EQUIPMENT} \\ \text{SCOPE-TEKTRONICS} \\ \text{475 OR EQUIVALENT} \\ t_{2} \approx \frac{L_{coil} (C_{pk})}{V_{clamp}}$	+10 V -9.2 V t _r , t _f < 10 ns DUTY CYCLE = 1% RB AND RC ADJUSTED FOR DESIRED IB AND IC

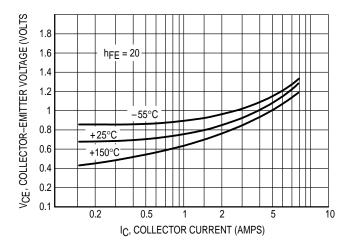


Figure 5. Inductive Switching Measurements

SAFE OPERATING AREA INFORMATION

FORWARD BIAS

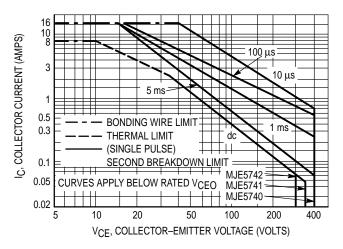
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC – VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_C=25^\circ C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \ge 25^\circ C$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 6 may be found at any case temperature by using the appropriate curve on Figure 1.

REVERSE BIAS

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base to emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as Reverse Bias Safe Operating Area and represents the voltage-current condition allowable during reverse biased turnoff. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Figure 7 gives the complete RBSOA characteristics.

The Safe Operating Area figures shown in Figures 6 and 7 are specified ratings for these devices under the test conditions shown.



16 14 C, COLLECTOR CURRENT (AMPS) 12 10 8 $V_{BE(off)} \le 5 V$ 6 T_J = 100°C MJE5742 MJE5741 MJE5740 0 0 100 200 400 500 VCE, COLLECTOR-EMITTER VOLTAGE (VOLTS)

Figure 6. Forward Bias Safe Operating Area

Figure 7. Reverse Bias Safe Operating Area

RESISTIVE SWITCHING PERFORMANCE

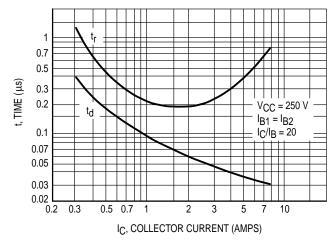


Figure 8. Turn-On Time

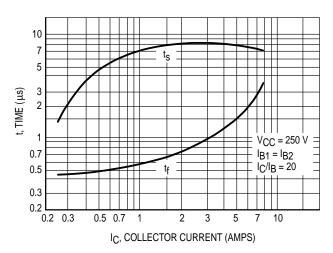
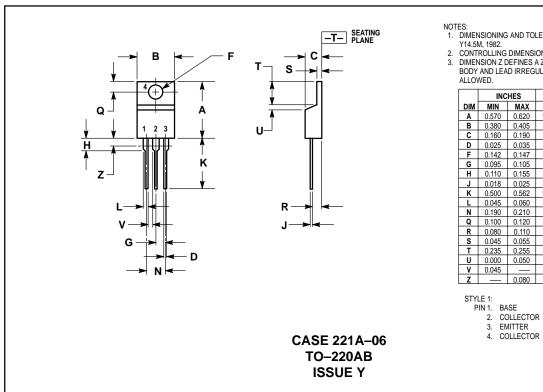


Figure 9. Turn-Off Time

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

MJE5740 MJE5741 MJE5742

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola exposure any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and CM are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



